

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

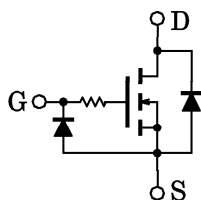
2SK1825

HIGH SPEED SWITCHING APPLICATIONS

ANALOG SWITCH APPLICATIONS

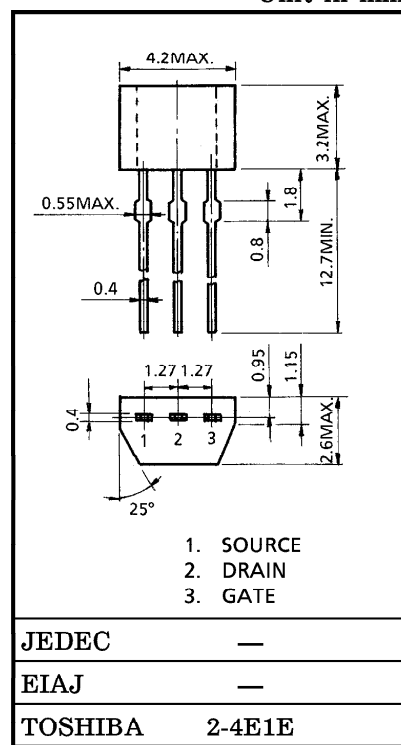
- 4V Gate Drive
- Low Threshold Voltage : $V_{th}=0.8\sim 2.5V$
- High Speed
- Enhancement-Mode
- Small Package

EQUIVALENT CIRCUIT



This transistor is electrostatic sensitive device.
Please handle with caution.

Unit in mm



JEDEC —

EIAJ —

TOSHIBA 2-4E1E

Weight : 0.13g (Typ.)

MAXIMUM RATINGS (T_a = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GSS}	10	V
DC Drain Current	I_D	50	mA
Drain Power Dissipation	P_D	300	mW
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	VGS=10V, VDS=0	—	—	1	μA
Drain-Source Breakdown Voltage		V (BR) DSS	ID=100μA, VGS=0	50	—	—	V
Drain Cut-off Current		IDSS	VDS=50V, VGS=0	—	—	1	μA
Gate Threshold Voltage		Vth	VDS=5V, ID=0.1mA	0.8	—	2.5	V
Forward Transfer Admittance		Yfs	VDS=5V, ID=10mA	20	—	—	mS
Drain-Source ON Resistance		RDS (ON)	ID=10mA, VGS=4.0V	—	20	50	Ω
Input Capacitance		Ciss	VDS=5V, VGS=0, f=1MHz	—	6.3	—	pF
Reverse Transfer Capacitance		Crss	VDS=5V, VGS=0, f=1MHz	—	1.3	—	pF
Output Capacitance		Coss	VDS=5V, VGS=0, f=1MHz	—	5.7	—	pF
Switching Time	Turn-on Time	ton	VDD=5V, ID=10mA, VGS=0~4.0V	—	0.11	—	μs
	Turn-off Time	toff	VDD=5V, ID=10mA, VGS=0~4.0V	—	0.15	—	μs

SWITCHING TIME TEST CIRCUIT

